

a parallel plate capacitor over said dielectric layer, said parallel plate capacitor extending into and out of said plurality of recesses in the semiconductor layer.

19. The integrated circuit of claim 18, wherein said parallel plate capacitor comprises a first polysilicon plate.

20. The integrated circuit of claim 19 wherein said parallel plate capacitor comprises a second polysilicon plate.

21. The integrated circuit of claim 18, wherein said parallel plate capacitor comprises a capacitor dielectric of PZT.

22. The integrated circuit of claim 18, wherein said parallel plate capacitor comprises a capacitor dielectric of silicon dioxide.

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